Supplementary Information’s to

**Molecular beam epitaxy growth of non-magnetic Weyl semimetal LaAlGe thin film**

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**TABLE S1.** Positional parameters of atoms in LaAlGe and occupancy (Occ) with important distances in fractional coordinates.

|  |  |  |  |  |
| --- | --- | --- | --- | --- |
| Atom | *x* | *y* | *z* | Occ |
| La | 0 | 0 | 0 | 1 |
| Al | 0 | 0 | 0.582 | 1 |
| Ge | 0 | 0 | 0.416 | 1 |

**TABLE S2.** The quantitative results of EDS analyses taken from four different spots of a film shown as an inset Figure 2(f).

|  |  |  |  |
| --- | --- | --- | --- |
| spot | La (Atomic %) | Al (Atomic %) | Ge (Atomic %) |
| 1 | 35.1 | 31.4 | 33.5 |
| 2 | 34.1 | 33.3 | 32.6 |
| 3 | 33.7 | 32.2 | 34.1 |
| 4 | 33.9 | 31.1 | 35 |
| Mean | 34.2 | 32 | 33.8 |
| S.D. | ~0.62 | ~0.98 | ~1 |

The estimated average atomic (%) ratio of La:Al:Ge is equal to 34.2:32:33.8.

The standard deviation of atomic (%) of La, Al, and Ge are 0.62, 0.98, and 1 respectively, which is very close to the expected stoichiometry of 1:1:1.